**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	210	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2.1	3.5	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2 SC-70 (SOT323)	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX138BKW	SC-70	plastic surface-mounted package; 3 leads	SOT323			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX138BKW	B8%

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V		
$V_{GS}$	gate-source voltage			-20	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	210	mA		
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	135	mA		
		$V_{GS}$ = 10 V; $T_{sp}$ = 25 °C		-	330	mA		
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	855	mA		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	266	mW		
			[1]	-	321	mW		
		T <sub>sp</sub> = 25 °C		-	1.33	W		
Tj	junction temperature			-55	150	°C		
T <sub>amb</sub>	ambient temperature			-55	150	°C		
T <sub>stg</sub>	storage temperature			-65	150	°C		
Source-drain	Source-drain diode							
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	210	mA		

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### 60 V, N-channel Trench MOSFET

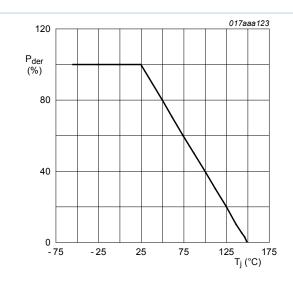


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

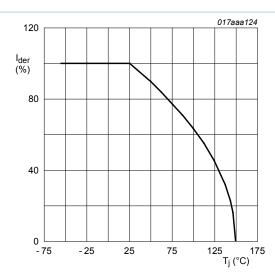


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

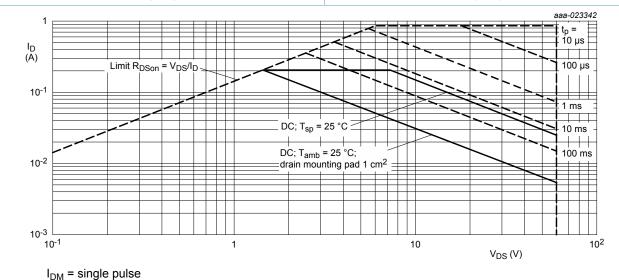


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	410	470	K/W
	from junction to ambient		[2]	-	340	390	K/W

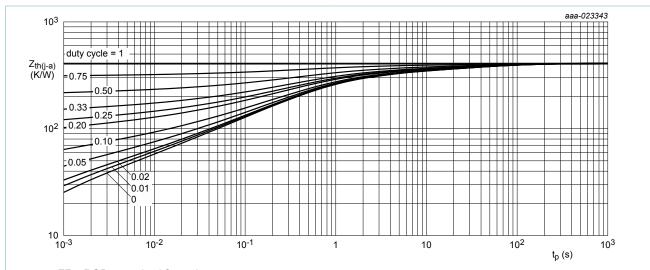
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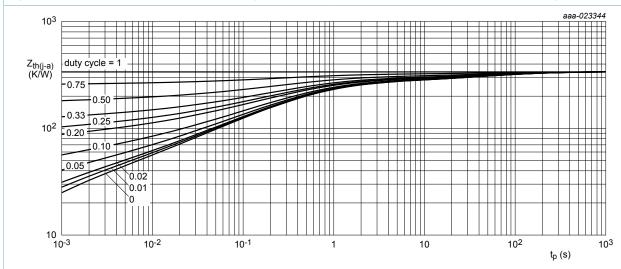
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	75	85	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μA
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μA
200	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C	-	2.1	3.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.3	7.2	Ω
		$V_{GS} = 5 \text{ V}; I_D = 170 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	2.2	3.8	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 75 \text{ mA}; T_j = 25 \text{ °C}$	-	2.6	5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	0.7	-	S
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 10 \text{ V};$	-	0.5	0.7	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.12	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	20	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	3.1	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	2	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	8	12	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	in diode		ı		1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 200 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.9	1.2	V

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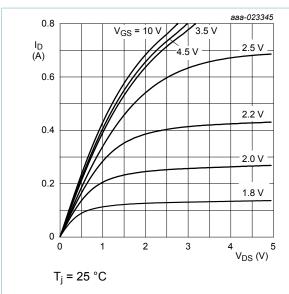


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

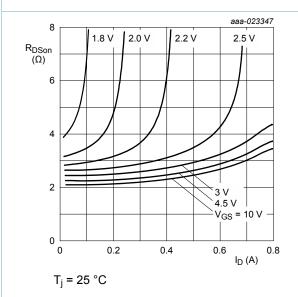


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

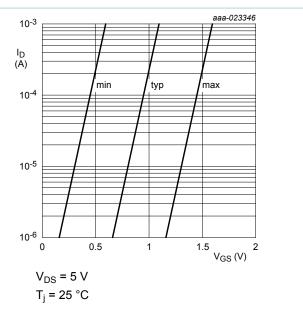


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

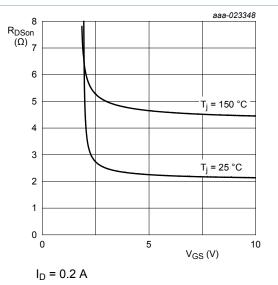


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, N-channel Trench MOSFET

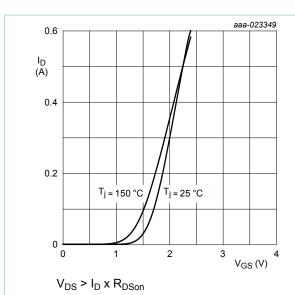


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

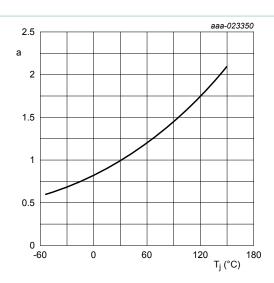


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

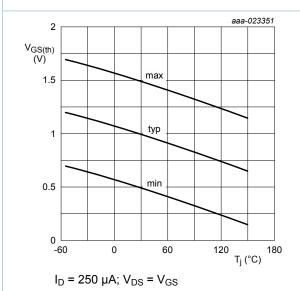
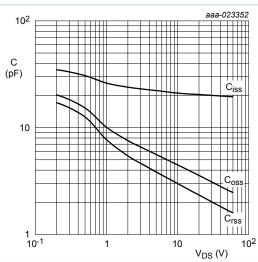


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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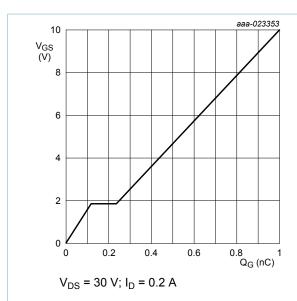


Fig. 14. Gate-source voltage as a function of gate charge; typical values

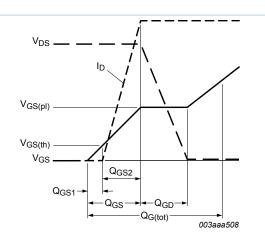


Fig. 15. MOSFET transistor: Gate charge waveform definitions

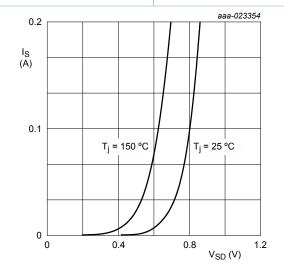
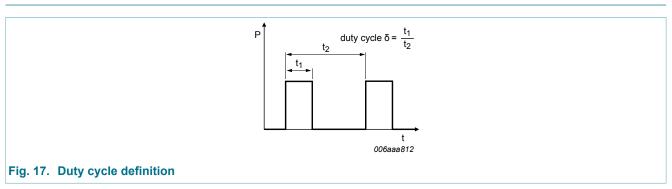


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



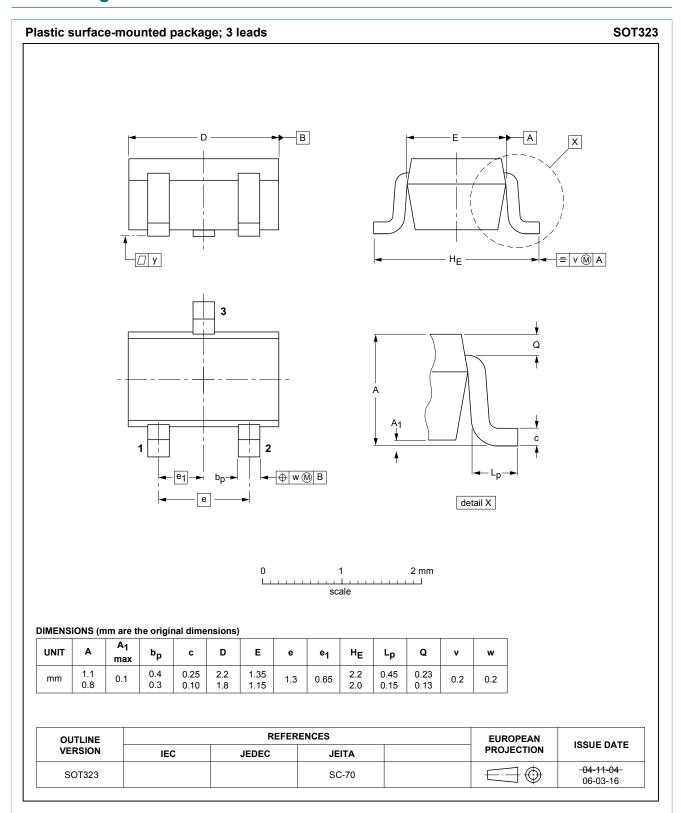
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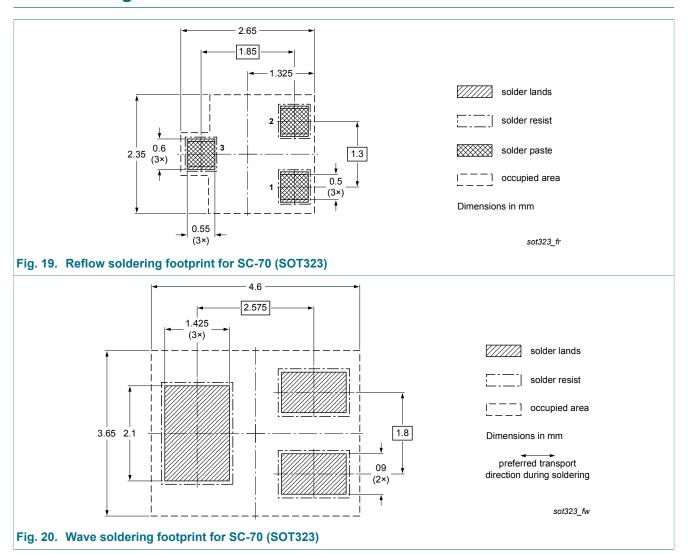
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## 12. Package outline



#### 60 V, N-channel Trench MOSFET

## 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BKW v.1	20160615	Product data sheet	-	-

#### 60 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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